NSN 5961-01-157-5859

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-157-5859 **Inclosure Material:** Metal **Overall Length:** 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 off-state voltage, rms total **Current Rating Per Characteristic:** 100.00 milliamperes forward current, total rms peak **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 81349-mil-s-19500/438 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: